

30 V, 0.7 A, Low $V_{CE(sat)}$ PNP Transistor

NSS30070MR6T1G

onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- This Device is Pb-Free and is RoHS Compliant

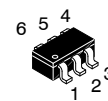
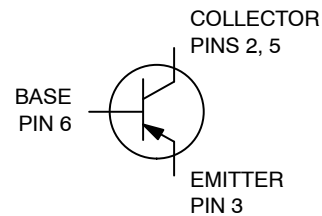
MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	700	mA
Base Current	I_B	350	mA
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	342	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	P_D	178	mW
Thermal Resistance - Junction-to-Ambient (Note 1)	$R_{\theta JA}$	366	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	665	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	P_D	346	mW
Thermal Resistance - Junction-to-Ambient (Note 2)	$R_{\theta JA}$	188	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

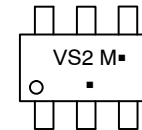
1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.

30 VOLTS
0.7 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 320 m Ω



SC-74
CASE 318F
STYLE 2

DEVICE MARKING



VS2 = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS30070MR6T1G	SC-74 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS30070MR6T1G

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage (I _C = 100 μA)	V _{(BR)CBO}	40	-	-	V
Collector-Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	30	-	-	V
Emitter-Base Breakdown Voltage (I _E = 100 μA)	V _{(BR)EBO}	5.0	-	-	V
Collector Cutoff Current (V _{CB} = 25 V, I _E = 0 A) (V _{CB} = 25 V, I _E = 0 A, T _A = 125°C)	I _{CBO}	-	-	1.0 10	μA
Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0 A)	I _{EBO}	-	-	10	μA
ON CHARACTERISTICS					
DC Current Gain (V _{CE} = 3.0 V, I _C = 100 mA)	h _{FE}	150	-	-	V
Collector-Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	-	0.25	V
Collector-Emitter Saturation Voltage (I _C = 700 mA, I _B = 70 mA)	V _{CE(sat)}	-	-	0.4	V
Base-Emitter Saturation Voltage (I _C = 700 mA, I _B = 70 mA)	V _{BE(sat)}	-	-	1.1	V
Base-Emitter Turn-On Voltage (I _C = 700 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	-	1.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

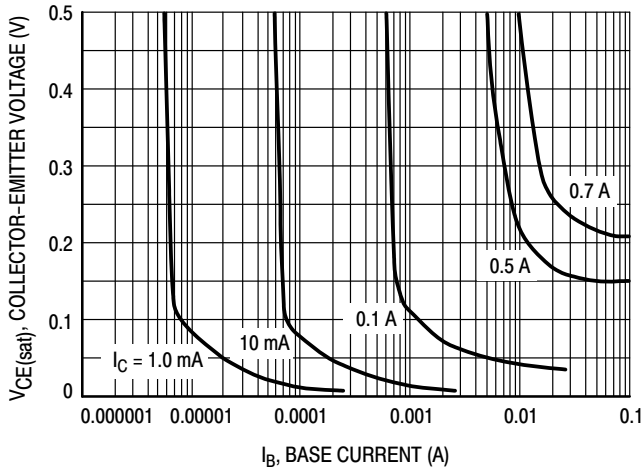


Figure 1. Collector Saturation Region

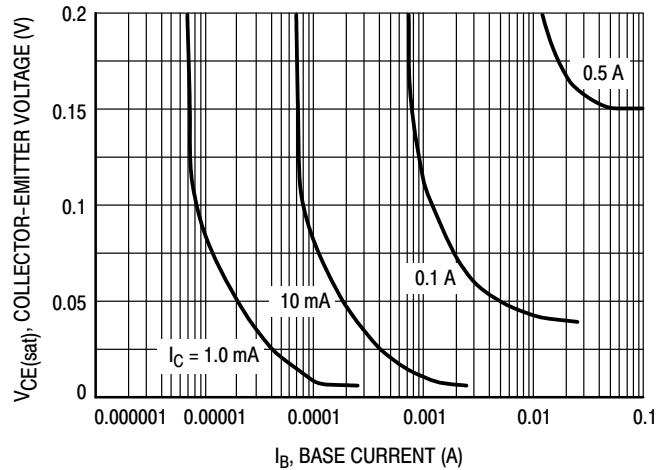


Figure 2. Collector Saturation Region

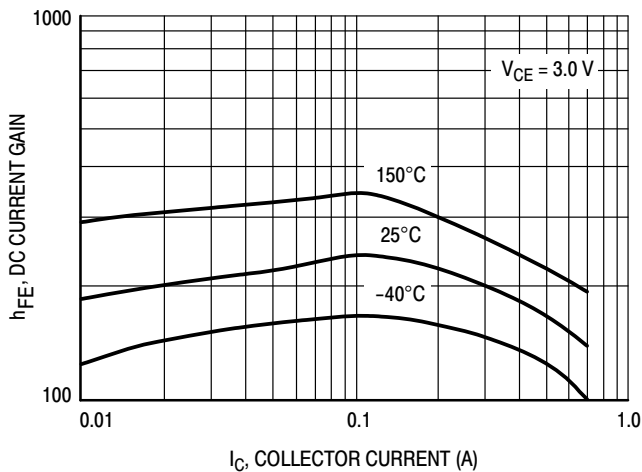


Figure 3. DC Current Gain

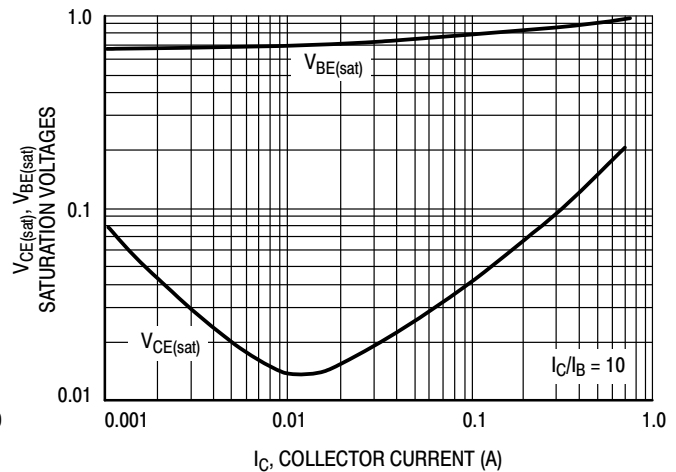


Figure 4. "SAT" Voltages

NSS30070MR6T1G

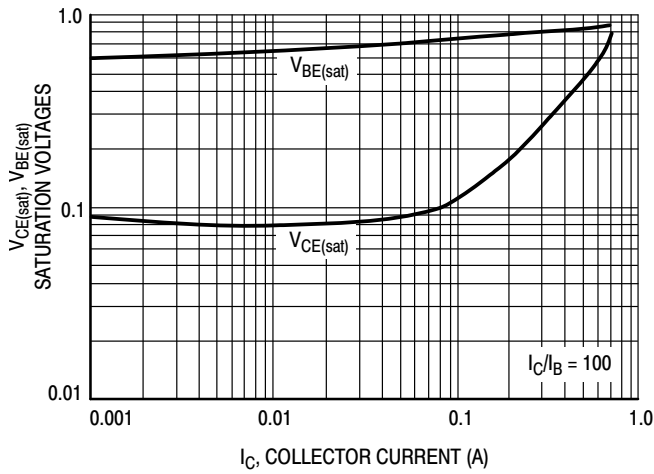


Figure 5. "SAT" Voltages

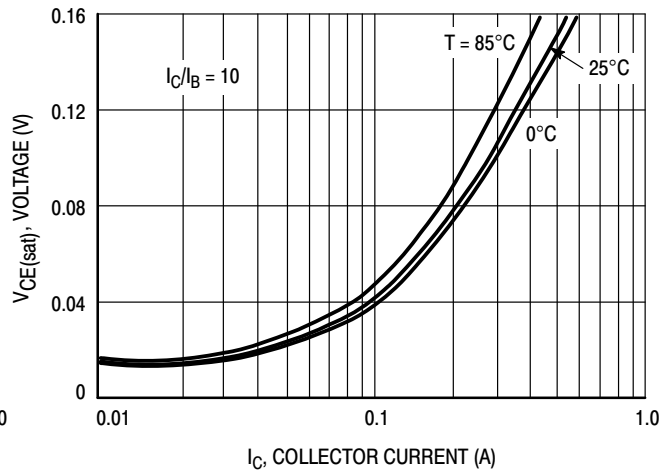


Figure 6. Collector-Emitter Saturation Voltage

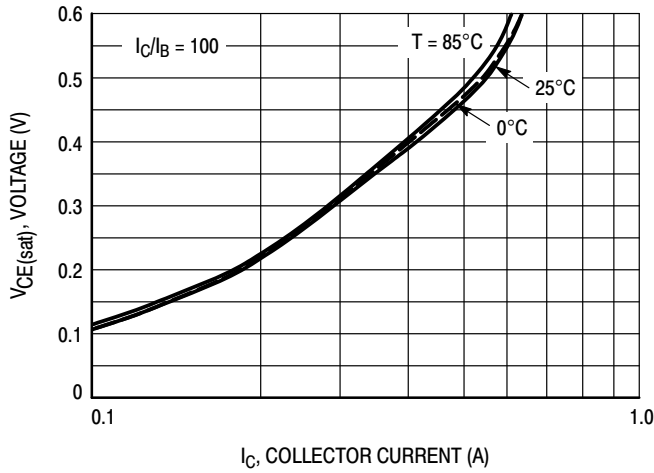


Figure 7. Collector-Emitter Saturation Voltage

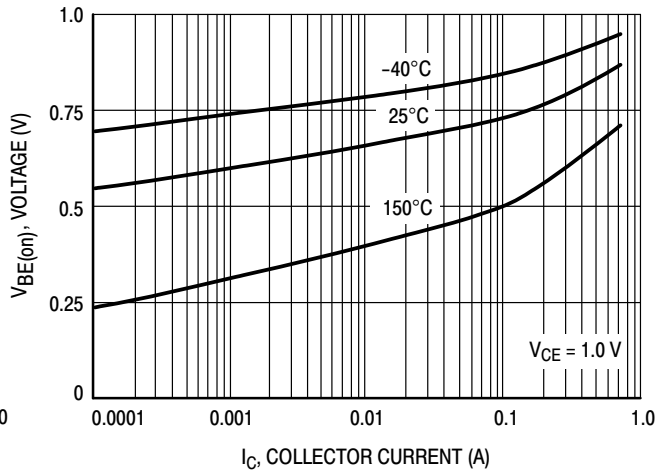


Figure 8. $V_{BE(on)}$ Voltage

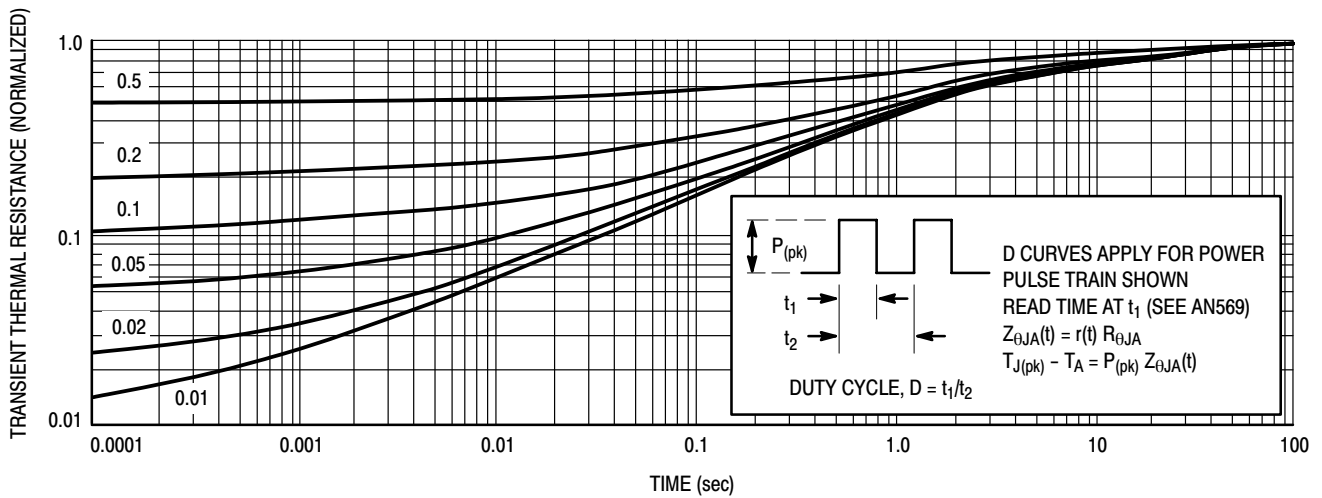


Figure 9. Thermal Response Curve

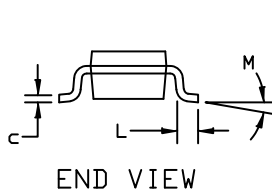
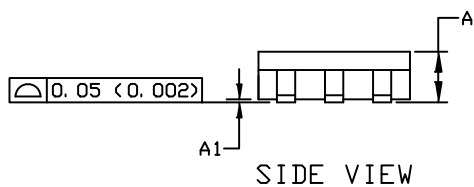
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



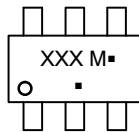
SCALE 2:1

SC-74
CASE 318F
ISSUE P

DATE 07 OCT 2021



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
HE	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0*	---	10*	0*	---	10*



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

STYLE 1:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. ANODE
- 6. CATHODE

STYLE 2:

- PIN 1. NO CONNECTION
- 2. COLLECTOR
- 3. EMITTER
- 4. NO CONNECTION
- 5. COLLECTOR
- 6. BASE

STYLE 3:

- PIN 1. EMITTER 1
- 2. BASE 1
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 2
- 6. COLLECTOR 1

STYLE 4:

- PIN 1. COLLECTOR 2
- 2. EMITTER 1/EMITTER 2
- 3. COLLECTOR 1
- 4. EMITTER 3
- 5. BASE 1/BASE 2/COLLECTOR 3
- 6. BASE 3

STYLE 5:

- PIN 1. CHANNEL 1
- 2. ANODE
- 3. CHANNEL 2
- 4. CHANNEL 3
- 5. CATHODE
- 6. CHANNEL 4

STYLE 6:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. CATHODE
- 5. CATHODE
- 6. CATHODE

STYLE 7:

- PIN 1. SOURCE 1
- 2. GATE 1
- 3. DRAIN 2
- 4. SOURCE 2
- 5. GATE 2
- 6. DRAIN 1

STYLE 8:

- PIN 1. EMITTER 1
- 2. BASE 2
- 3. COLLECTOR 2
- 4. EMITTER 2
- 5. BASE 1
- 6. COLLECTOR 1

STYLE 9:

- PIN 1. EMITTER 2
- 2. BASE 2
- 3. COLLECTOR 1
- 4. EMITTER 1
- 5. BASE 1
- 6. COLLECTOR 2

STYLE 10:

- PIN 1. ANODE/CATHODE
- 2. BASE
- 3. EMITTER
- 4. COLLECTOR
- 5. ANODE
- 6. CATHODE

STYLE 11:

- PIN 1. EMITTER
- 2. BASE
- 3. ANODE/CATHODE
- 4. ANODE
- 5. CATHODE
- 6. COLLECTOR

DOCUMENT NUMBER:	98ASB42973B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-74	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales